Octal D-Type Flip-Flop with 3-State Outputs

With 5V-Tolerant Inputs

The MC74LVX374 is an advanced high speed CMOS octal D-type flip-flop with 3-state outputs. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

This 8-bit D-type flip-flop is controlled by a clock input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

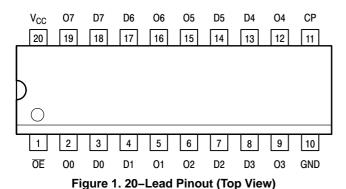
Features

- High Speed: $f_{max} = 160 \text{ MHz}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs

- Dow Noise: V_{OLP} = 0.8 V (Max)
 Pin and Function Compatible with Other Standard Logic Families
 Latchup Performance Exceeds 300 mA
 ESD Performance:

Human Body Model > 2000 V: Machine Model > 200 V

Pb–Free Packages are Available³

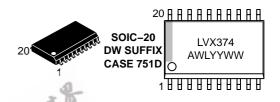


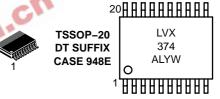
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

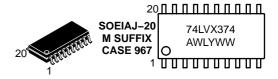


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MARKING DIAGRAMS







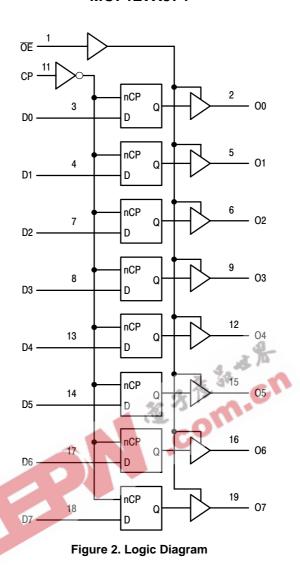
= Assembly Location L, WL = Wafer Lot Y, YY Year = Work Week W. WW

PIN NAMES

Pins	Function
OE	Output Enable Input
CP	Clock Pulse Input
D0-D7	Data Inputs
O0-O7	3-State Outputs

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.



INPUTS			OUTPUTS	
ŌĒ	СР	Dn	On	OPERATING MODE
L L	↑	l h	L H	Load and Read Register
L	1	Х	NC	Hold and Read Register
Н	1	Х	Z	Hold and Disable Outputs
H H	↑	l h	Z Z	Load Internal Register and Disable Outputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

DC ELECTRICAL CHARACTERISTICS

			Vcc	Т	A = 25°	С	T _A = - 40) to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50\mu A$ $I_{OH} = -50\mu A$ $I_{OH} = -4mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OL} = 50\mu A$ $I_{OL} = 50\mu A$ $I_{OL} = 4mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	V _{in} = 5.5V or GND	3.6			±0.1		±1.0	μΑ
I _{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			4.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

				Т	A = 25°	С	$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Con	ditions	Min	Тур	Max	Min	Max	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$	60 45	115 60		50 40		MHz
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	100 60	160 95		85 55		
t _{PLH} , t _{PHL}	Propagation Delay CP to O	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$		8.5 11.0	16.3 19.8	1.0 1.0	19.5 23.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		6.7 9.2	10.6 14.1	1.0 1.0	12.5 16.0	
t _{PZL} , t _{PZH}	Output Enable Time OE to O	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.6 10.1	14.5 18.0	1.0 1.0	17.5 21.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.9 8.4	9.3 12.8	1.0 1.0	11.0 14.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OE to O	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	C _L = 50pF		11.5	18.5	1.0	22.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	$C_L = 50pF$		9.6	13.2	1.0	15.0	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50pF$ $C_L = 50pF$	40	4 万	1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

		Т	A = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance		6				pF
C _{PD}	Power Dissipation Capacitance (Note 2)		32				pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per flip–flop). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0 \text{ns}$)

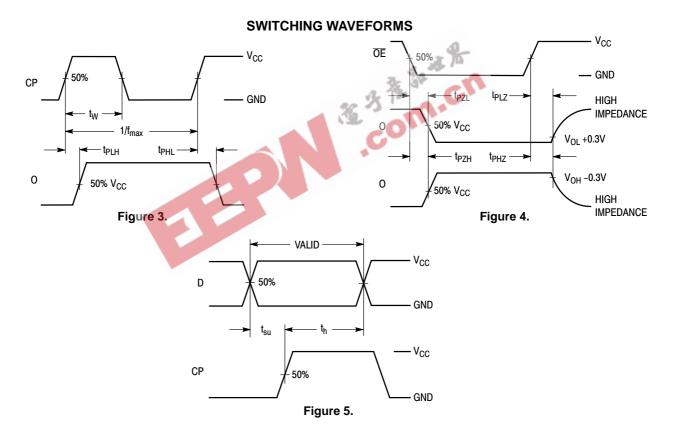
•			T _A =	25°C	5° C $T_{A} = -40 \text{ to } 85^{\circ}$ C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _w	Minimum Pulse Width, CP	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$		7.5 5.0	8.0 5.5	ns
t _{su}	Minimum Setup Time, D to CP	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$		6.5 4.5	6.5 4.5	ns
t _h	Minimum Hold Time, D to CP	V _{CC} = 2.7V V _{CC} = 3.3 ±0.3V		2.0 2.0	2.0 2.0	ns

ORDERING INFORMATION

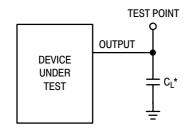
Device	Package	Shipping [†]
MC74LVX374DWR2	SOIC-20	1000 Tape & Reel
MC74LVX374DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LVX374DTR2	TSSOP-20*	2500 Tape & Reel
MC74LVX374M	SOEIAJ-20	50 Units / Rail
MC74LVX374MG	374MG SOEIAJ-20 (Pb-Free)	
MC74LVX374MEL	SOEIAJ-20	2000 Tape & Reel
MC74LVX374MELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

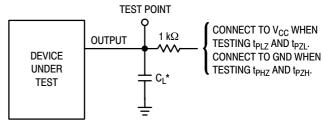


TEST CIRCUITS



^{*}Includes all probe and jig capacitance

Figure 6. Propagation Delay Test Circuit

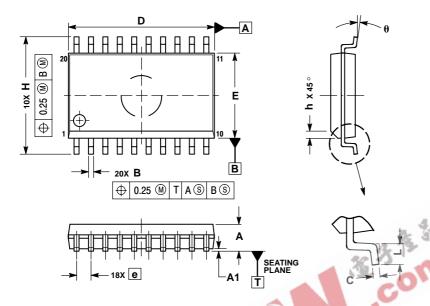


*Includes all probe and jig capacitance

Figure 7. Three-State Test Circuit

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



NOTES

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION
- PROTRUSION.

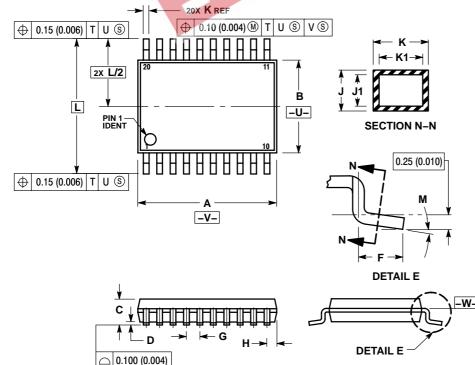
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN MAX				
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
_ D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
≥ L	0.50	0.90			
θ	0°	7 °			

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



-T- SEATING PLANE

NOTES:

- DIES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

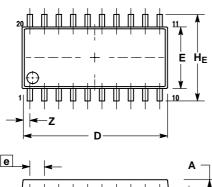
 2. CONTROLLING DIMENSION:
 MILLIMETER.

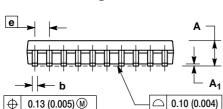
- MILLIME I ER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

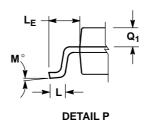
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

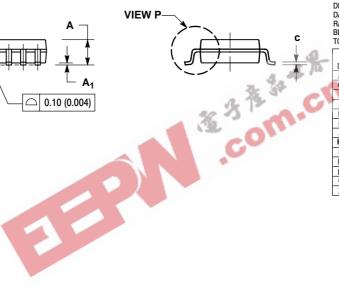
PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. STAFFICIONS D AND E DO NOT INCLUDE MOLD 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR
- AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.81		0.032



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